

● General Description

The AGM402H combines advanced trench MOSFET technology with a low resistance package to provide extremely low $R_{DS(ON)}$.

This device is ideal for load switch and battery protection applications.

● Features

- Advance high cell density Trench technology
- Low $R_{DS(ON)}$ to minimize conductive loss
- Low Gate Charge for fast switching
- Low Thermal resistance

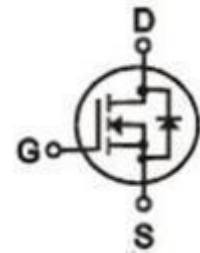
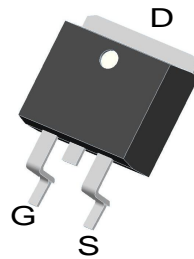
● Application

- MB/VGA Vcore
- SMPS 2nd Synchronous Rectifier
- POL application
- BLDC Motor driver

Product Summary

BVDSS	RDS(ON)	ID
40V	2.6mΩ	170A

TO-263 Pin Configuration



Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
AGM402H	AGM402H	TO-263	----	----	800

Table 1. Absolute Maximum Ratings (TA=25°C)

Symbol	Parameter	Value	Unit
VDS	Drain-Source Voltage (VGS=0V)	40	V
VGS	Gate-Source Voltage (VDS=0V)	±20	V
ID	Drain Current-Continuous(Tc=25°C) (Note 1)	170	A
	Drain Current-Continuous(Tc=100°C)	98	A
IDM (pluse)	Drain Current-Continuous@ Current-Pulsed (Note 2)	570	A
PD	Maximum Power Dissipation(Tc=25°C)	250	w
	Maximum Power Dissipation(Tc=100°C)	100	w
EAS	Avalanche energy (Note 3)	1000	mJ
TJ,TSTG	Operating Junction and Storage Temperature Range	-55 To 150	°C

Table 2. Thermal Characteristic

Symbol	Parameter	Typ	Max	Unit
RθJA	Thermal Resistance Junction-ambient (Steady State) ¹	---	62	°C/W
RθJC	Thermal Resistance Junction-Case ¹	---	0.5	°C/W

Table 3. Electrical Characteristics (TA=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
On/Off States						
BVDSS	Drain-Source Breakdown Voltage	VGS=0V ID=250μA	40	45	--	V
IDSS	Zero Gate Voltage Drain Current	VDS=40V, VGS=0V	--	--	1	μA
IGSS	Gate-Body Leakage Current	VGS=±20V, VDS=0V	--	--	±100	nA
VGS(th)	Gate Threshold Voltage	VDS=VGS, ID=250μA	1.0	1.7	2.5	V
gFS	Forward Transconductance	VDS=10V, ID=20A	--	--	--	S
RDS(on)	Drain-Source On-State Resistance	VGS=10V, ID=40A	--	2.6	3.8	mΩ
		VGS=4.5V, ID=20A	--	3.3	5.0	mΩ
Dynamic Characteristics						
Ciss	Input Capacitance	VDS=20V, VGS=0V, F=1MHZ	--	4140	--	pF
Coss	Output Capacitance		--	405	--	pF
Crss	Reverse Transfer Capacitance		--	360	--	pF
Rg	Gate resistance	VGS=0V, VDS=0V, f=1.0MHz	--	2	--	Ω
Switching Times						
td(on)	Turn-on Delay Time	VGS=10V, VDS=20V ID=40A, RGEN=3Ω	--	13.7	--	nS
tr	Turn-on Rise Time		--	6.1	--	nS
td(off)	Turn-Off Delay Time		--	50	--	nS
tf	Turn-Off Fall Time		--	10	--	nS
Qg	Total Gate Charge	VGS=20V, VDS=20V, ID=40A	--	73	--	nC
Qgs	Gate-Source Charge		--	15	--	nC
Qgd	Gate-Drain Charge		--	15	--	nC
Source-Drain Diode Characteristics						
ISD	Source-Drain Current(Body Diode)		--	--	170	A
VSD	Forward on Voltage	VGS=0V, IS=40A	--	0.8	1.2	V
trr	Reverse Recovery Time	IS=40A , di/dt=500A/μs , TJ=25°C	--	18	--	ns
Qrr	Reverse Recovery Charge		--	40	--	nc

Notes 1.The maximum current rating is package limited.

Notes 2.Repetitive Rating: Pulse width limited by maximum junction temperature

Notes 3.EAS condition: TJ=25°C

Typical Characteristics

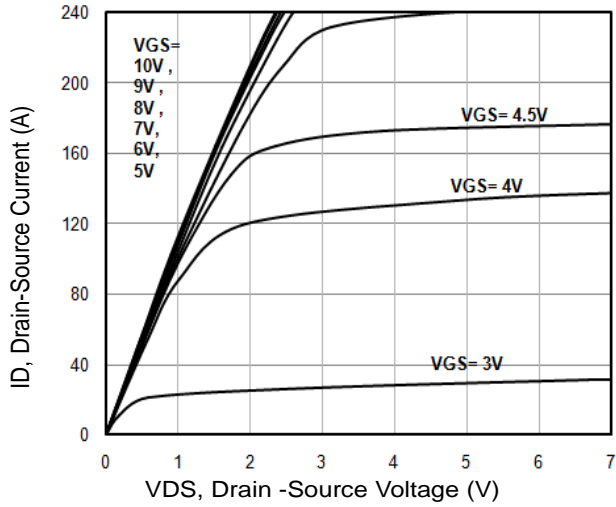


Fig1. Typical Output Characteristics

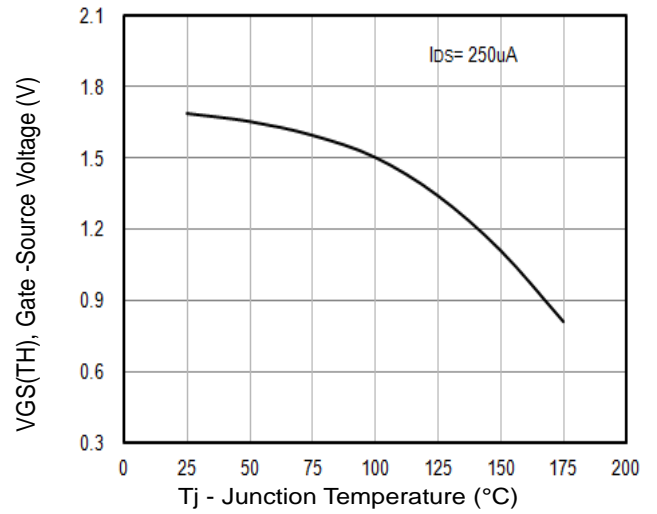


Fig2. $V_{GS(TH)}$ Gate-Source Voltage Vs. T_j

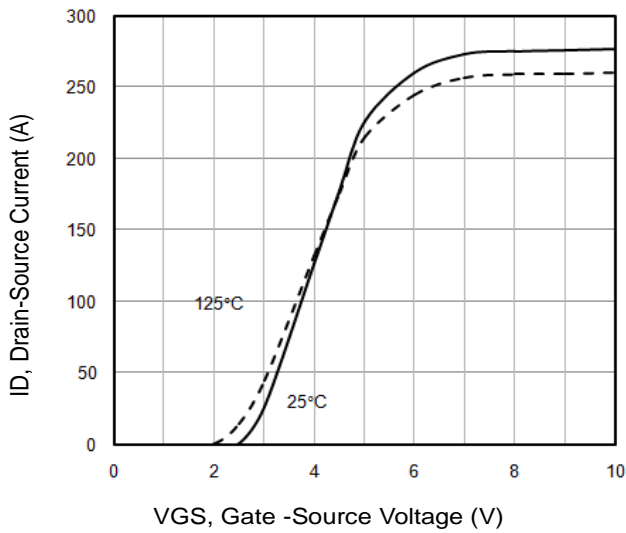


Fig3. Typical Transfer Characteristics

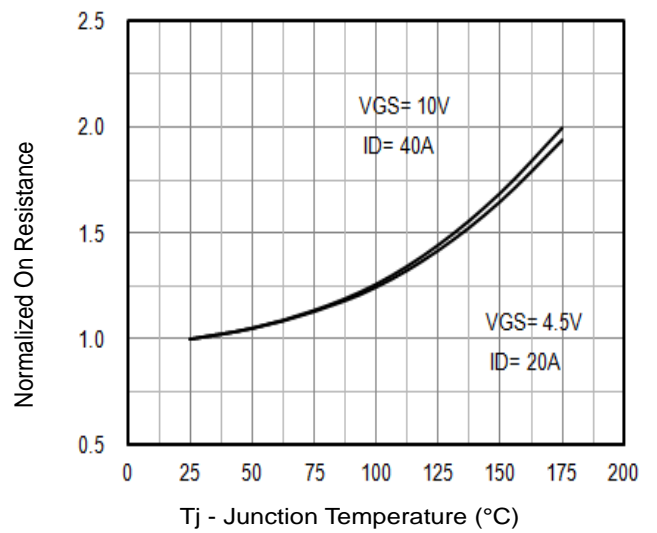


Fig4. Normalized On-Resistance Vs. Temperature

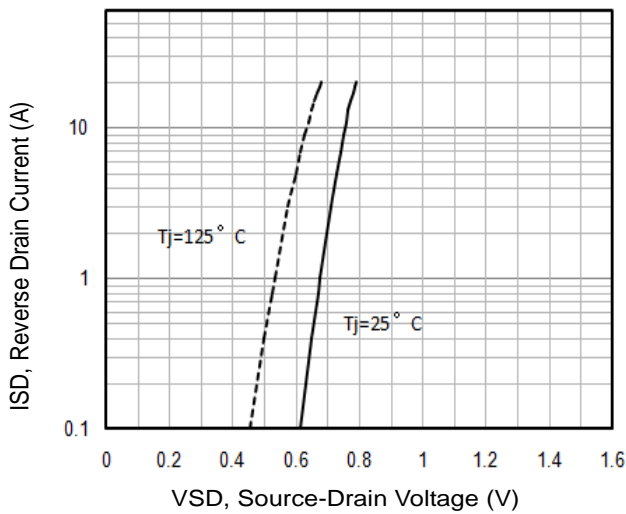


Fig5. Typical Source-Drain Diode Forward Voltage

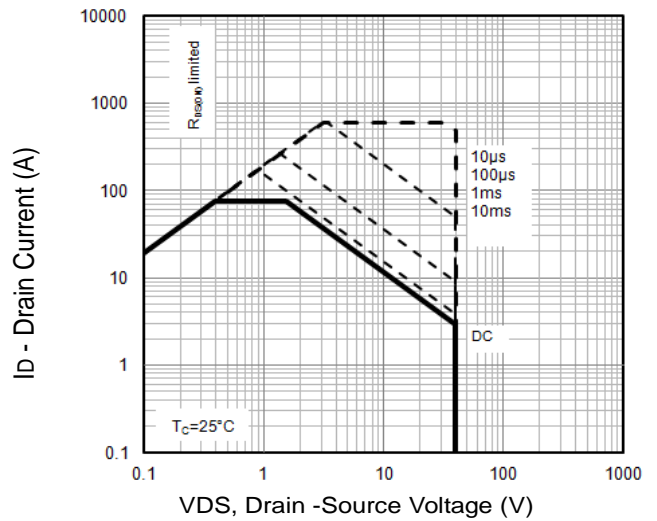


Fig6. Maximum Safe Operating Area

Typical Characteristics

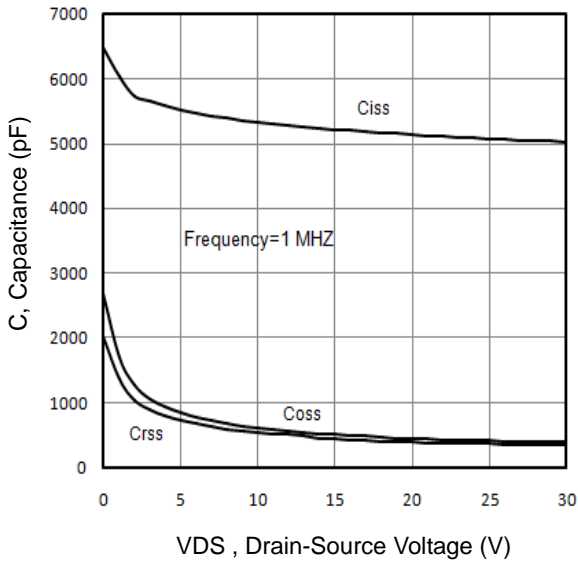


Fig7. Typical Capacitance Vs. Drain-Source Voltage

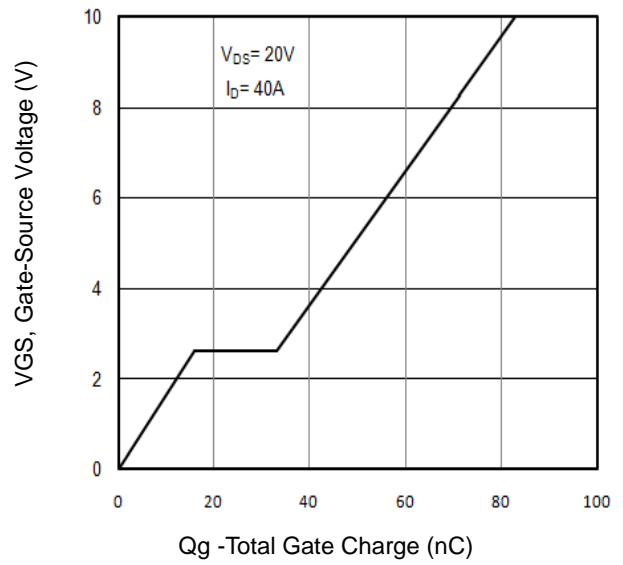


Fig8. Typical Gate Charge Vs. Gate-Source Voltage

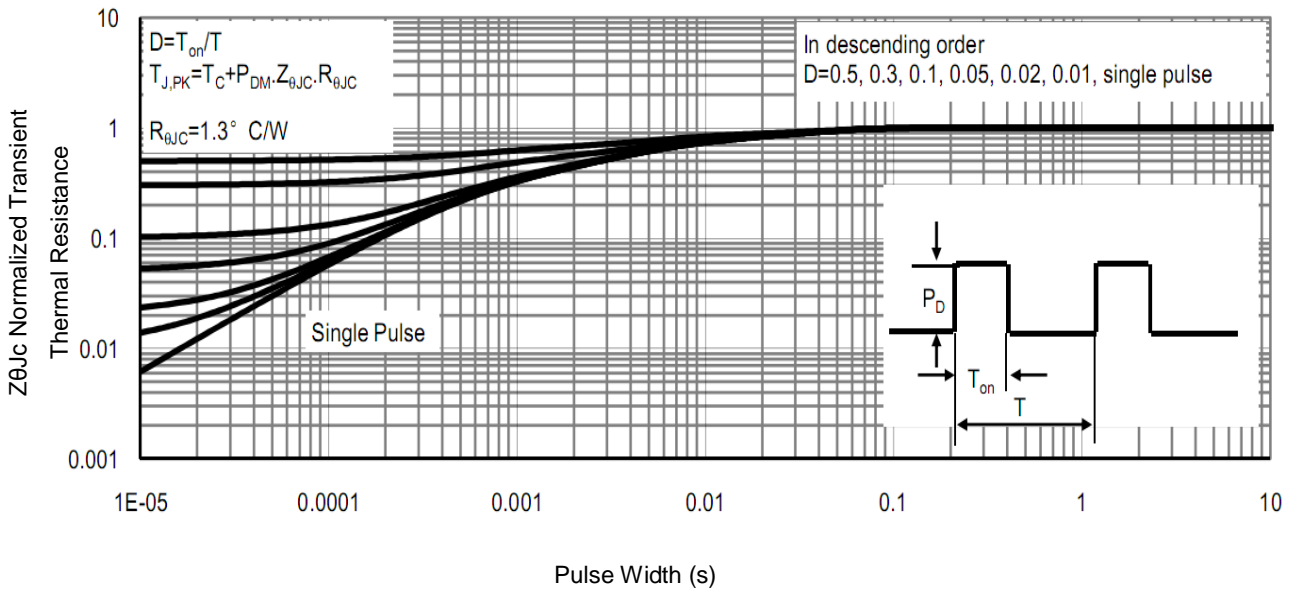


Fig9 . Normalized Maximum Transient Thermal Impedance

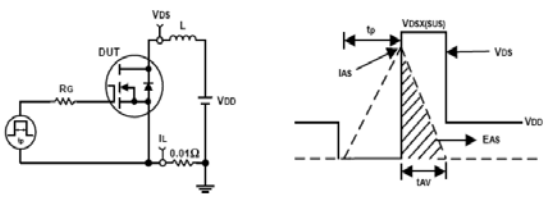


Fig10. Unclamped Inductive Test Circuit and waveforms

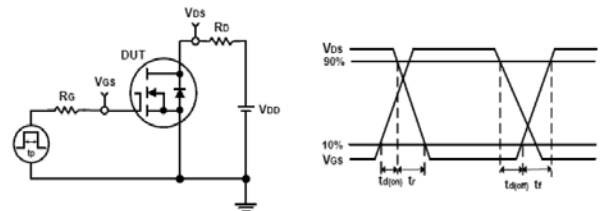
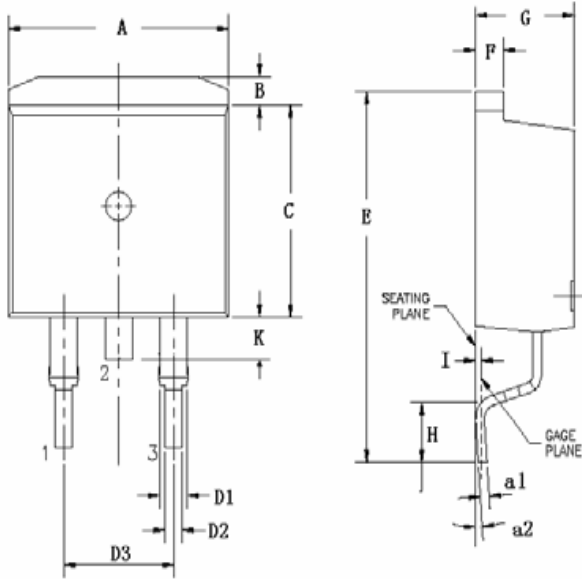


Fig11. Switching Time Test Circuit and waveforms

TO-263, 2 leads

Dimensions in mm unless otherwise specified



Symbol	Min	Nom	Max
A	9.66	9.97	10.28
B	1.02	1.17	1.32
C	8.59	9.00	9.40
D1	1.14	1.27	1.40
D2	0.70	0.83	0.95
D3		5.08	
E	15.09	15.24	15.39
F	1.15	1.28	1.40
G	4.30	4.50	4.70
H	2.29	2.54	2.79
I		0.25	
K	1.30	1.45	1.60
a1	0.45	0.55	0.65
a2(degree)	0°		8°


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